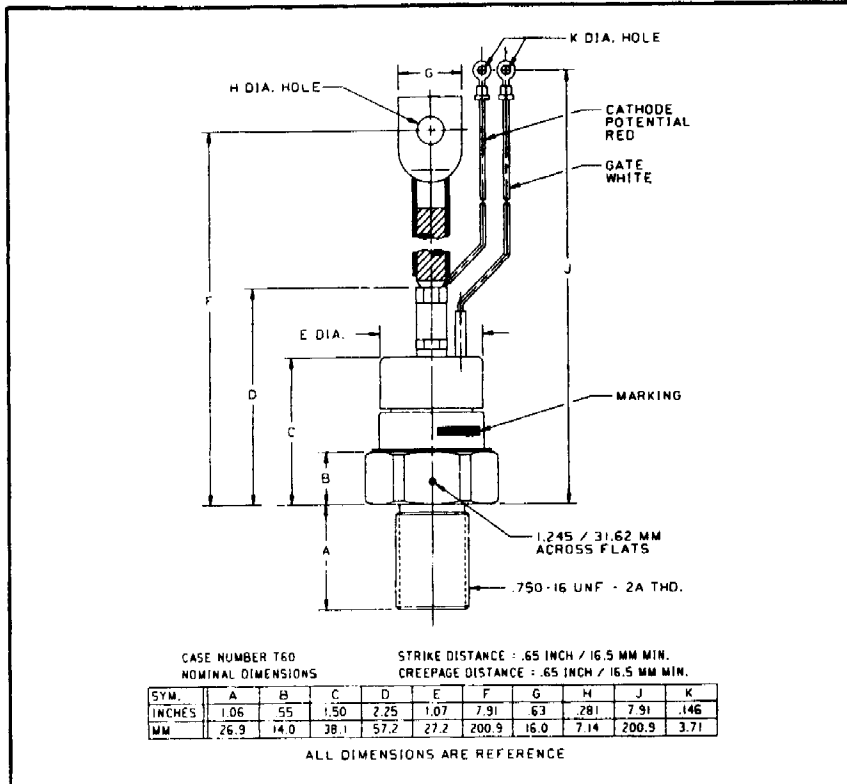


New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005

Phase Control SCR
175 Amperes Average
1200 Volts

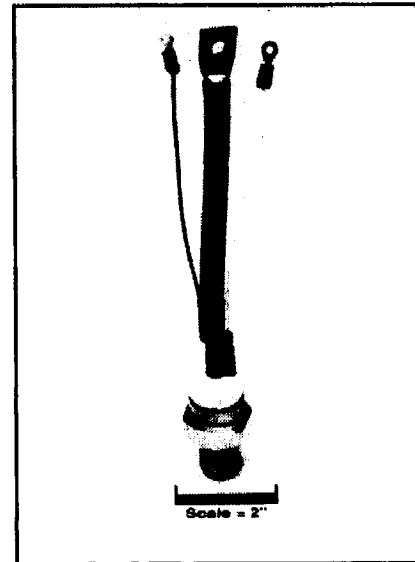


2N3884-2N3895 (Outline Drawing)

Ordering Information:

Select the complete six digit part number you desire from the table, i.e. 2N3895 is a 1200 Volt, 175 Ampere Phase Control SCR.

Type	Voltage		Current
	V _{DRM}	V _{RRM}	
2N3884	50		175
2N3885	100		
2N3886	200		
2N3887	300		
2N3888	400		
2N3889	500		
2N3890	600		
2N3891	700		
2N3892	800		
2N3893	900		
2N3894	1000		
2N3895	1200		



2N3884-2N3895
Phase Control SCR
175 Amperes Average, 1200 Volts

Description:

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, compression bonded encapsulated (CBE) devices employing the field-proven amplifying (di/namic) gate.

Features:

- Low On-State Voltage
- High di/dt
- High dv/dt
- Hermetic Packaging
- Excellent Surge and I²t Ratings

Applications:

- Power Supplies
- Battery Chargers
- Motor Control

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2N3884-2N3895
Phase Control SCR
175 Amperes Average, 1200 Volts

Electrical and Thermal Characteristics

Characteristics	Symbol	Test Conditions	2N3884-3895	Units
Voltage—Blocking State Maximums				
Forward Leakage, Peak	I_{DFM}	$T_J = 125^\circ\text{C}, V_{DFM} = \text{rated}$	25	mA
Reverse Leakage, Peak	I_{RFM}	$T_J = 125^\circ\text{C}, V_{RFM} = \text{rated}$	25	mA
Current—Conducting State Maximums				
Peak On-State Voltage	V_{TM}	$I_{TM} = 625\text{A}, T_J = 25^\circ\text{C}$	1.55	Volts
Switching				
Typical Turn-Off Time	t_t	$I_T = 150\text{A}, T_J = 125^\circ\text{C},$ $di_T/dt = 12.5\text{A}/\mu\text{sec},$ reapplied $dv/dt = 20\text{V}/\mu\text{sec}$ linear to $0.8 V_{DFM}$	100	μsec
Typical Turn-On Time	t_{on}	$I_T = 100\text{A}, V_D = 100\text{V}$	5	μsec
Min. Critical dv/dt exponential to V_{DFM}	dv/dt	$T_J = 125^\circ\text{C}$	300	$\text{V}/\mu\text{sec}$
Thermal				
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$.13	$^\circ\text{C}/\text{Watt}$
Case to Sink, Lubricated	$R_{\theta CS}$.075	$^\circ\text{C}/\text{Watt}$
Gate—Maximum Parameters				
Gate Current to Trigger	I_{GT}	$T_J = 25^\circ\text{C}, V_D = 12\text{V}$	150	mA
Gate Voltage to Trigger	V_{GT}	$T_J = 25^\circ\text{C}, V_D = 12\text{V}$	3	Volts
Non-Triggering Gate Voltage	V_{GDM}	$T_J = 125^\circ\text{C}, V = \text{rated } V_{DFM}$.15	Volts
Peak Forward Gate Current	I_{GTM}		4	Amperes
Peak Reverse Gate Voltage	V_{GRM}		5	Volts



Quality Semi-Conductors

New Jersey Semi-Conductor Products, Inc.

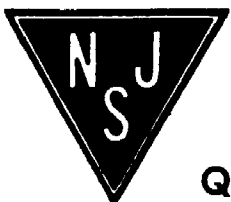
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2N3884-2N3885
Phase Control SCR
175Amperes Average, 1200 Volts

Absolute Maximum Ratings

	Symbol	2N3884-3885	Units
RMS On-State Current	$I_{T(RMS)}$	275	Amperes
Average On-State Current	$I_{T(av)}$	175	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (60Hz)	I_{TSM}	4500	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (50Hz)	I_{TSM}	4100	Amperes
Critical Rate-of-Rise of On-State Current (Non-Repetitive)	di/dt	800	Amperes/ μ s
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	150	Amperes/ μ s
I^2t (for Fusing), 8.3 milliseconds	I^2t	84,000	A ² sec
Peak Gate Power Dissipation	P_{GM}	15	Watts
Average Gate Power Dissipation	$P_{GM(av)}$	3	Watts
Storage Temperature	T_{STG}	-40 to 150	°C
Operating Temperature	T_J	-40 to 125	°C
Mounting Torque		300	in.-lb.
Mounting Torque		340	kg-cm



Quality Semi-Conductors